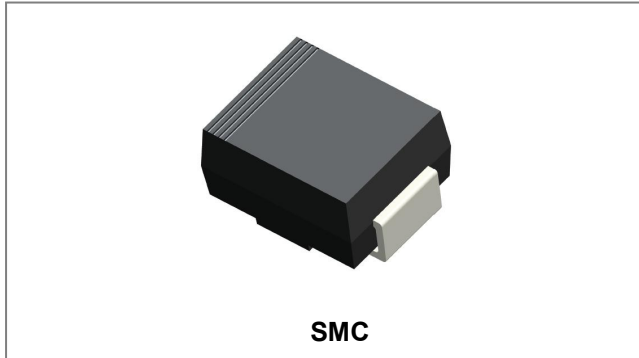


SK34 SCHOTTKY RECTIFIER



Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- High Current Capability
- Low Power Loss, High Efficiency
- High Surge Current Capability
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- This is a Pb - Free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	40	V
Average Rectified Forward Current	$I_F (AV)$	50% duty cycle @ $T_C = 105^\circ\text{C}$, rectangular wave form	3	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse, $T_c = 25^\circ\text{C}$	75	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 3A, Pulse, $T_J = 25^\circ\text{C}$	0.58	0.63	V
	V_{F1}	@ 3A, Pulse, $T_J = 125^\circ\text{C}$	0.50	0.57	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R$, $T_J = 25^\circ\text{C}$	0.01	50	μA
	I_{R2}	@ $V_R = \text{rated } V_R$, $T_J = 100^\circ\text{C}$	-	10	mA
Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25^\circ\text{C}$, $f_{SIG} = 1\text{MHz}$	45	150	pF
Series Inductance	L_S	Measured lead to lead 5 mm from package body	8.0	-	nH
Voltage Rate of Change	dv/dt	-	-	10,000	V/ μs

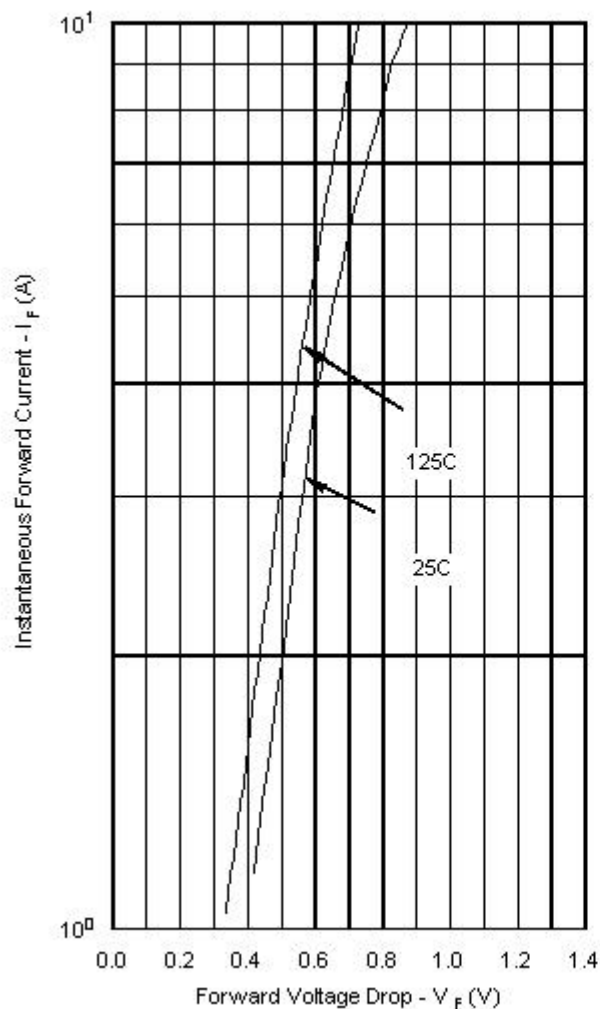
* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

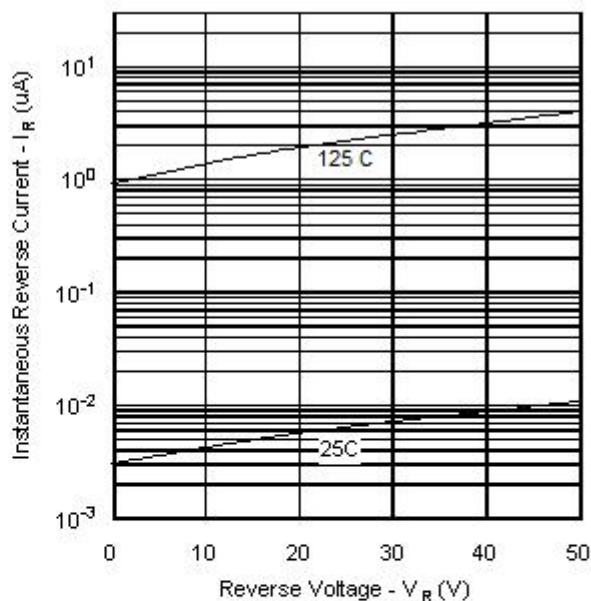
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Repetitive Peak Reverse Current	I_{RRM}	$T_p=2\mu s$ $F=1KHZ$ square	1	A
Repetitive Peak Avalanche Power	P_{ARM}	$T_p=2\mu s$ $T_J=25^\circ C$	1300	W
Approximate Weight	wt	-	0.21	g

Ratings and Characteristics Curves

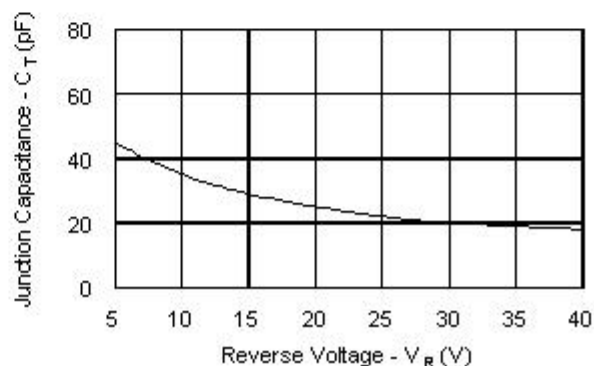
Typical Forward Characteristics



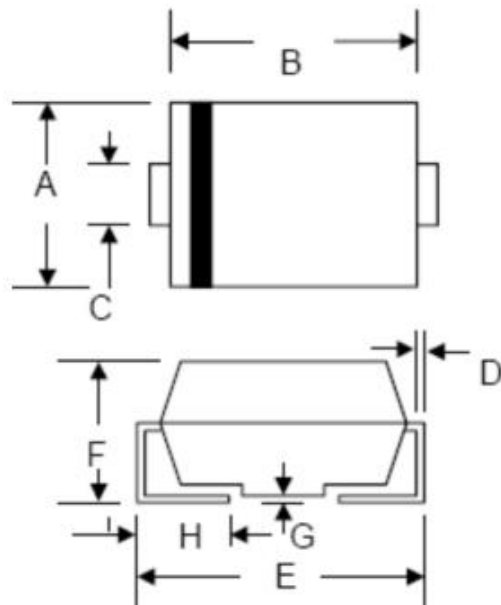
Typical Reverse Characteristics



Typical Junction Capacitance



Mechanical Dimensions SMC



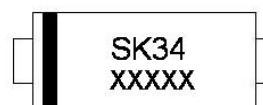
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	5.59	6.22	0.220	0.245
B	6.60	7.11	0.260	0.280
C	2.75	3.25	0.108	0.128
D	0.152	0.305	0.006	0.012
E	7.75	8.25	0.305	0.325
F	2.00	2.95	0.079	0.116
G	0.051	0.203	0.002	0.008
H	0.76	1.60	0.030	0.063

Ordering Information

Device	Package	Shipping
SK34	SMC	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

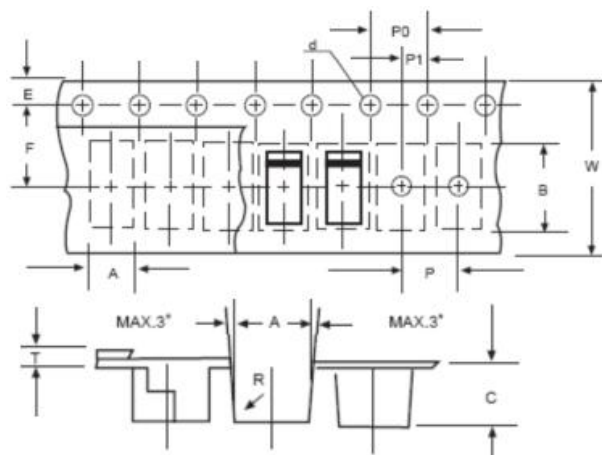


Where XXXXX is YYWWL

SK = Device Type
3 = Forward Current (3A)
4 = Reverse Voltage (40V)
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape & Reel Specification SMC



SYMBOL	Millimeters	
	Min.	Max.
A	5.90	6.10
B	8.20	8.40
C	2.40	2.60
d	1.40	1.60
E	1.40	1.60
F	7.60	7.70
P	7.90	8.10
P0	3.90	4.10
P1	3.90	4.10
T	-	0.600
W	15.80	16.20

Technical Data
Data Sheet N0102, Rev. B



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